

# Zhenyu Yang

## List of Publications by Year in descending order

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19  
papers

1,128  
citations

759233

12  
h-index

794594

19  
g-index

19  
all docs

19  
docs citations

19  
times ranked

2201  
citing authors

#	ARTICLE	IF	CITATIONS
1	On-Chip Detection of Multiwavelength Surface Plasmon Polaritons Based on Plasmonic Demultiplexers. ACS Photonics, 2022, 9, 391-397.	6.6	12
2	MoS <sub>2</sub> Nanoribbon Transistor for Logic Electronics. IEEE Transactions on Electron Devices, 2022, 69, 3433-3438.	3.0	1
3	Electrode Engineering in MoS <sub>2</sub> MOSFET: Different Semiconductor/Metal Interfaces. Advanced Electronic Materials, 2022, 8, .	5.1	5
4	High-current MoS <sub>2</sub> transistors with non-planar gate configuration. Science Bulletin, 2021, 66, 777-782.	9.0	12
5	Advanced tape-exfoliated method for preparing large-area 2D monolayers: a review. 2D Materials, 2021, 8, 032002.	4.4	30
6	InGaZnO Tunnel and Junction Transistors Based on Vertically Stacked Black Phosphorus/InGaZnO Heterojunctions. Advanced Electronic Materials, 2020, 6, 2000291.	5.1	11
7	The photovoltaic and photoconductive photodetector based on GeSe/2D semiconductor van der Waals heterostructure. Applied Physics Letters, 2020, 116, .	3.3	30
8	Cladded Surface-Plasmon-Enhanced BP Photodetector Based on the Damage-Free Metal-Semiconductor Interface. IEEE Transactions on Electron Devices, 2020, , 1-4.	3.0	5
9	High-Performance Photoinduced Memory with Ultrafast Charge Transfer Based on MoS <sub>2</sub> /SWCNTs Network Van Der Waals Heterostructure. Small, 2019, 15, e1804661.	10.0	42
10	Enhanced Photoresponsivity of a GaAs Nanowire Metal-Semiconductor-Metal Photodetector by Adjusting the Fermi Level. ACS Applied Materials & Interfaces, 2019, 11, 33188-33193.	8.0	151
11	Interface engineering for two-dimensional semiconductor transistors. Nano Today, 2019, 25, 122-134.	11.9	35
12	WSe <sub>2</sub> /GeSe heterojunction photodiode with giant gate tunability. Nano Energy, 2018, 49, 103-108.	16.0	73
13	Black Phosphorus Infrared Photodetectors with Fast Response and High Photoresponsivity. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800310.	2.4	28
14	MoS <sub>2</sub> Negative-Capacitance Field-Effect Transistors with Subthreshold Swing below the Physics Limit. Advanced Materials, 2018, 30, e1800932.	21.0	87
15	Metal-Ion-Modified Black Phosphorus with Enhanced Stability and Transistor Performance. Advanced Materials, 2017, 29, 1703811.	21.0	431
16	Performance Limits of the Self-Aligned Nanowire Top-Gated MoS <sub>2</sub> Transistors. Advanced Functional Materials, 2017, 27, 1602250.	14.9	37
17	Controlled synthesis of high-quality crystals of monolayer MoS <sub>2</sub> for nanoelectronic device application. Science China Materials, 2016, 59, 182-190.	6.3	51
18	Enhancing Photoresponsivity of Self-Aligned MoS <sub>2</sub> Field-Effect Transistors by Piezo-Phototronic Effect from GaN Nanowires. ACS Nano, 2016, 10, 7451-7457.	14.6	86

#	ARTICLE	IF	CITATIONS
19	Comment on "Metal Semiconductor Field-Effect Transistor with MoS <sub>2</sub> /Conducting NiO <sub>x</sub> van der Waals Schottky Interface for Intrinsic High Mobility and Photoswitching Speed", ACS Nano, 2016, 10, 1714-1715.	14.6	1